

Features

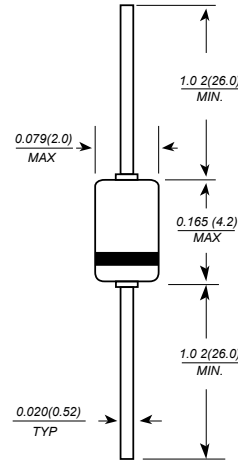
- Silicon Epitaxial Planar Diodes
- Micro Melf package

Mechanical Data

- Case : DO-35 Glass Case
- Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- Polarity : Color band denotes cathode end
- Mounting position : Any
- Weight : 0.13 gram (approximately)



DO-35(GLASS)



Dimensions in millimeters

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{RRM}	Maximum Repetitive Reverse Voltage	150	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	1.0 4.0	A A
T_{stg}	Storage Temperature Range	-65 to +200	$^\circ\text{C}$
T_J	Operating Junction Temperature	175	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Units
P_D	Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	C/W

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Max	Units
V_R	Breakdown Voltage	$I_R = 100 \mu\text{A}$	150		V
V_F	Forward Voltage	$I_F = 1.0 \text{ mA}$ $I_F = 5.0 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 50 \text{ mA}$ $I_F = 100 \text{ mA}$ $I = 200 \text{ mA}$	0.52 0.60 0.65 0.75 0.79 0.83	0.68 0.75 0.80 0.88 0.92 1.00	V V V V V V
I_R	Reverse Current	$V_R = 125 \text{ V}$ $V_R = 30 \text{ V}, T_A = 125^\circ\text{C}$ $V_R = 125 \text{ V}, T_A = 125^\circ\text{C}$ $V_R = 125 \text{ V}, T_A = 150^\circ\text{C}$		1 0.3 0.5 3	nA μA μA μA
C_T	Total Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		8	pF
t_{rr}	Reverse Recovery Time	$I_F = 10 \text{ mA}, V_R = 3.5 \text{ V}, R = 1.0 \text{ k}\Omega$		3	μs